

IN THE CLAIMS:

Please cancel Claims 2 through 6, without prejudice.

1. (Currently amended) A semiconductor material having a equilibrium dopant solubility of boron or indium of greater than 1% wherein said semiconductor material comprises silicon grown on a Aluminum Phosphate (AIP) substrate along a (001) direction.

2. (Canceled)

3. (Canceled)

4. (Canceled).

5. (Canceled)

6. (Canceled)

7. (Currently Amended) The semiconductor material of claim 1 comprising
A a p-type semiconductor comprising silicon and a dopant comprising boron or
indium.

8. (Currently Amended) The semiconductor material of Claim 7 wherein
said dopant includes boron and said semiconductor comprises SiB₃ SiB₃.